

NPN-Silizium-Fototransistor Zeilen
Silicon NPN Phototransistor Arrays
Lead (Pb) Free Product - RoHS Compliant

BPX 80
BPX 82 ... 89



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 450 nm bis 1100 nm
- Hohe Linearität
- Mehrstellige Zeilenbauform aus klarem Epoxy

Features

- Especially suitable for applications from 450 nm to 1100 nm
- High linearity
- Multiple-digit array package of transparent epoxy

Anwendungen

- Miniaturlichtschranken
- Industrieelektronik
- „Messen/Steuern/Regeln“

Applications

- Miniature photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Fotostrom , $E_e = 0.5 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $V_{CE} = 5 \text{ V}$ Photocurrent $I_{PCE} \text{ (mA)}$
BPX 82	Q62702P0021	> 0.32
BPX 83	Q62702P0025	> 0.32
BPX 84	Q62702P0030	> 0.32
BPX 85	Q62702P0031	> 0.32
BPX 86	Q62702P0022	> 0.32
BPX 87	Q62702P0032	> 0.32
BPX 88	Q62702P0033	> 0.32
BPX 89	Q62702P0026	> 0.32
BPX 80	Q62702P0028	> 0.32

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 80	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	35	V
Kollektorstrom Collector current	I_C	50	mA
Kollektorspitzenstrom, $\tau < 10 \mu s$ Collector surge current	I_{CS}	200	mA
Verlustleistung, $T_A = 25 \text{ }^\circ\text{C}$ Total power dissipation	P_{tot}	90	mW
Wärmewiderstand Thermal resistance	R_{thJA}	750	K/W

Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 950\text{ nm}$)

Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	450 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.11	mm ²
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.5×0.5	mm × mm
Halbwinkel Half angle	φ	± 18	Grad deg.
Kapazität Capacitance $V_{\text{CE}} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_{CE}	7.5	pF
Dunkelstrom Dark current $V_{\text{CE}} = 20\text{ V}$, $E = 0$	I_{CEO}	1 (≤ 50)	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit Buchstaben gekennzeichnet.

The phototransistors are grouped according to their spectral sensitivity and distinguished by alphabetic characters.

Bezeichnung Parameter	Symbol Symbol	Werte Value			Einheit Unit
		-A	-B	-C	
Fotostrom Photocurrent $E_e = 0.5 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $V_{CE} = 5 \text{ V}$ $E_v = 1000 \text{ lx}$, Normlicht/standard light A, $V_{CE} = 5 \text{ V}$	I_{PCE} I_{PCE}	0.32...0.63 1.5	0.40...0.80 1.9	≥ 0.50 2.3	mA mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 1 \text{ k}\Omega$	t_r , t_f	5.5	6	8	μs
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$, $E_e = 0.5 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	V_{CEsat}	150	150	150	mV

1) I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

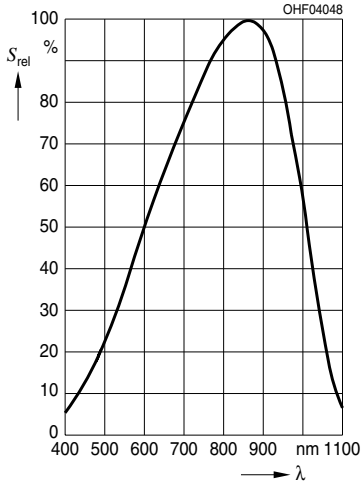
1) I_{PCEmin} is the min. photocurrent of the specified group.

Die gelieferten Bauelemente sind mit -A, -B, -C gekennzeichnet. Wegen Ausbeuteschwankungen ist jedoch die Bestellung einer definierten Gruppe -A, -B, -C nicht möglich.

For delivery the components are marked -A, -B, -C. Due to differing yields, it is not possible to order a definite group.

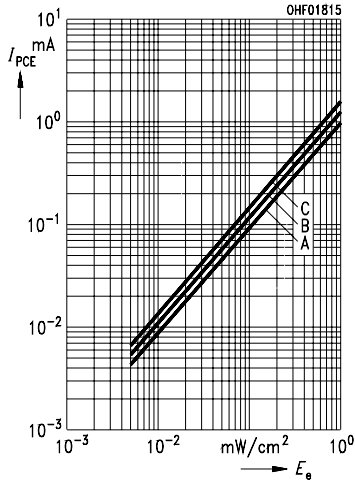
Relative Spectral Sensitivity

$S_{rel} = f(\lambda)$



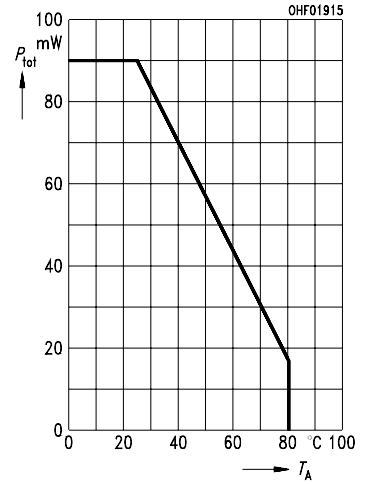
Photocurrent

$I_{PCE} = f(E_e), V_{CE} = 5 V$



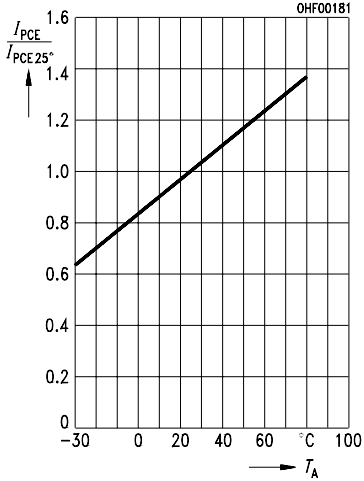
Total Power Dissipation

$P_{tot} = f(T_A)$



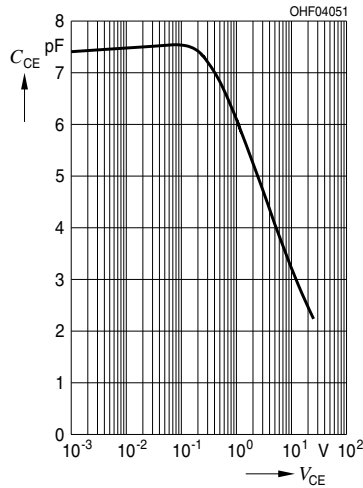
Photocurrent

$I_{PCE}/I_{PCE25^\circ} = f(T_A), V_{CE} = 5 V$



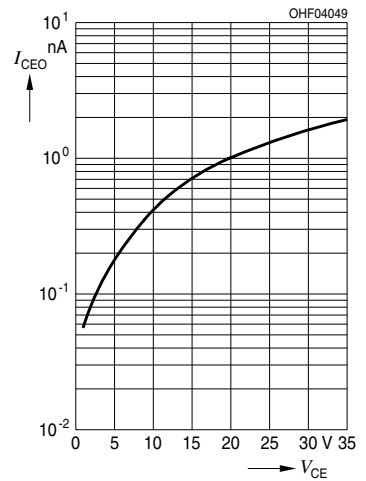
Collector-Emitter Capacitance

$C_{CE} = f(V_{CE}), f = 1 MHz, E = 0$



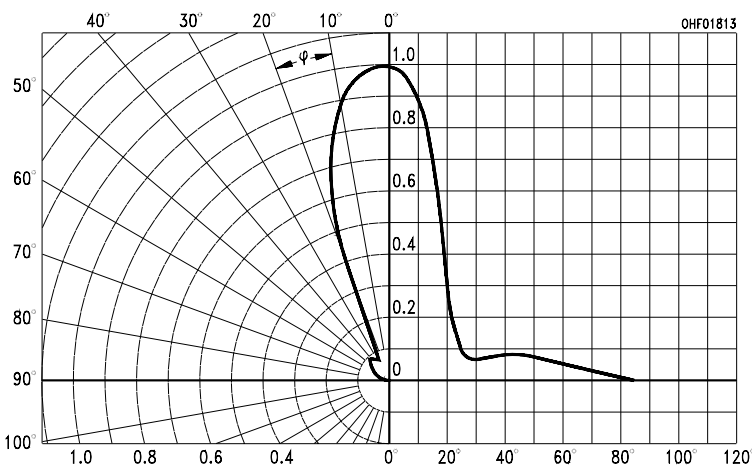
Dark Current

$I_{CEO} = f(V_{CE}), E = 0$



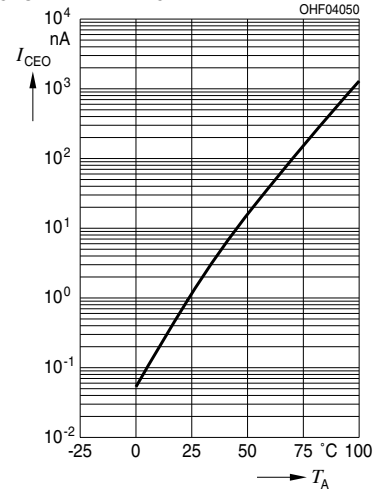
Directional Characteristics

$S_{rel} = f(\varphi)$

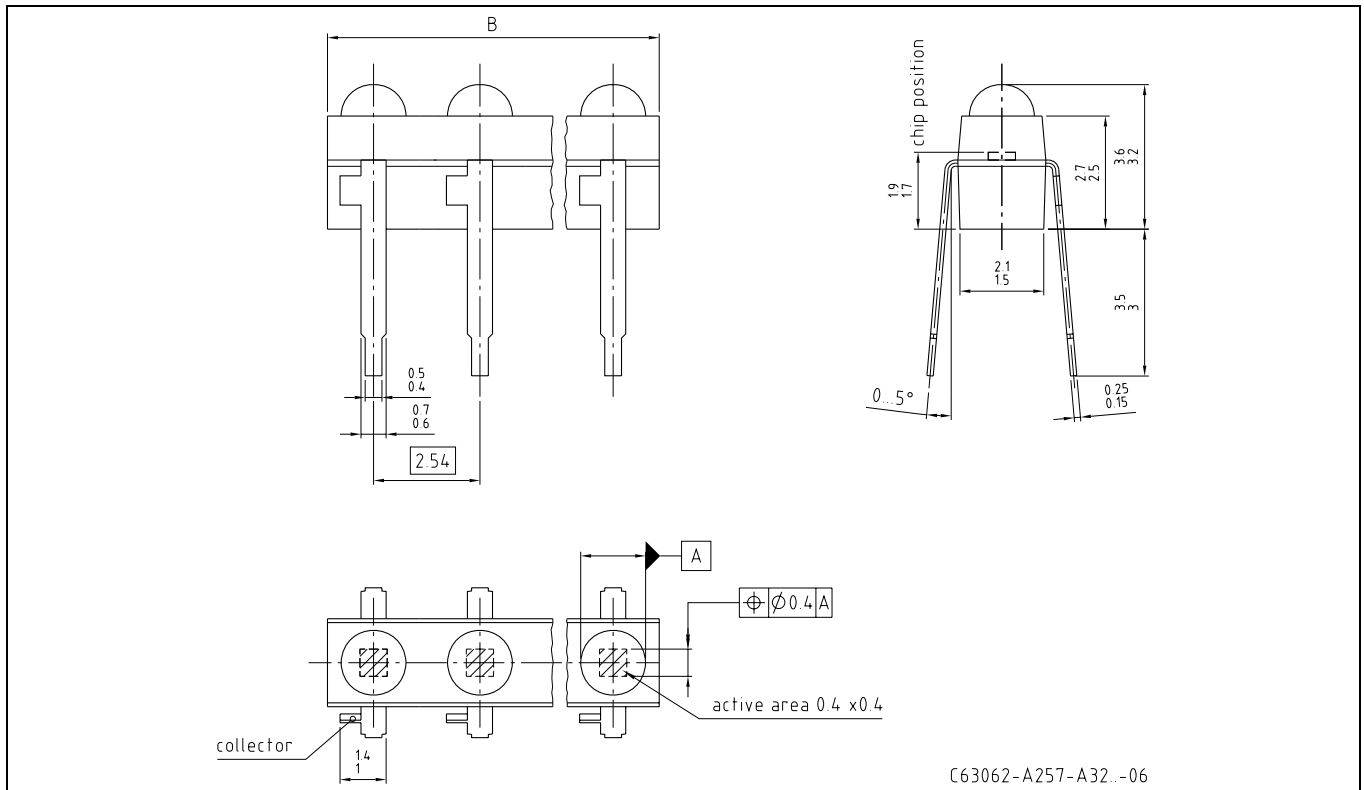


Dark Current

$I_{CEO} = f(T_A), V_{CE} = 20 V, E = 0$



Maßzeichnung
Package Outlines

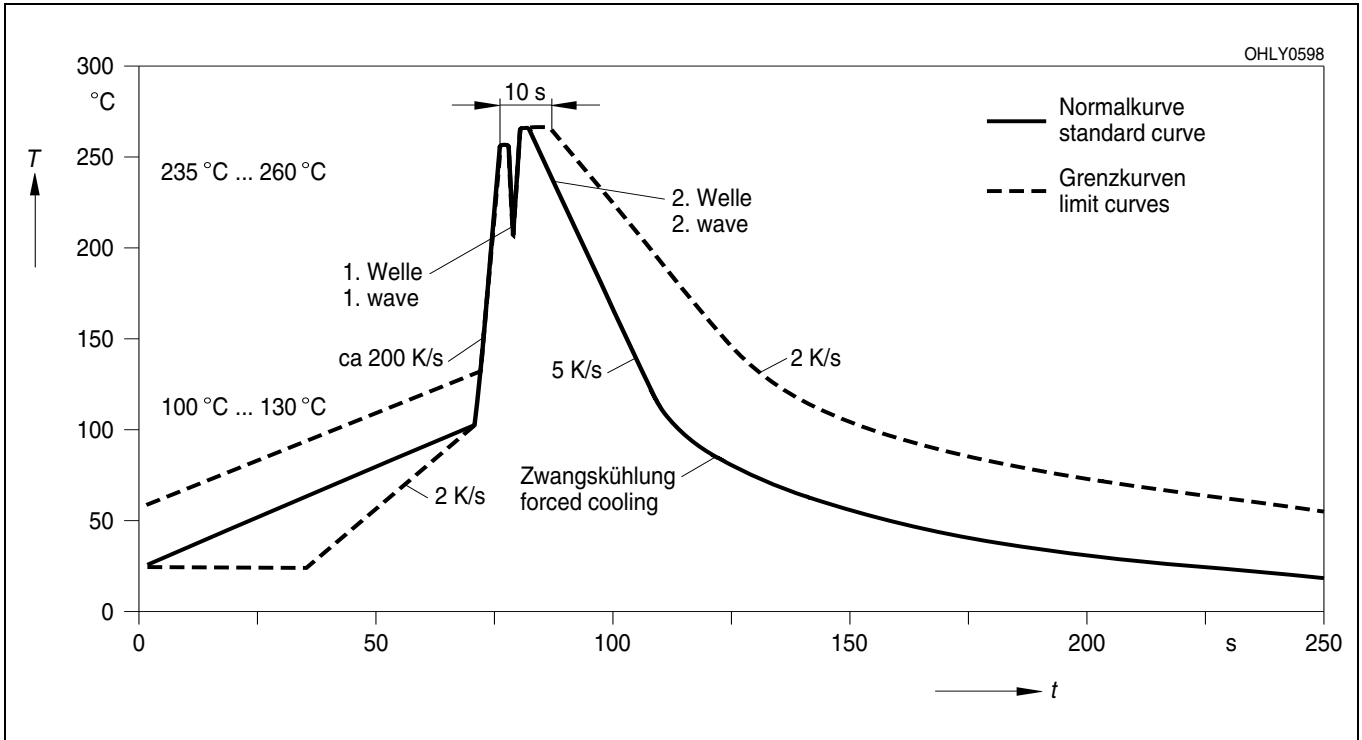


Maße in mm / Dimensions in mm.

Transistoren pro Zeile Number of Transistors per Array	Maß „B“ Dimension “B”
2	4.5 ... 4.9
3	7.0 ... 7.4
4	9.6 ... 10.0
5	12.1 ... 12.5
6	14.6 ... 16.0
7	17.2 ... 17.6
8	19.7 ... 20.1
9	22.3 ... 22.7
10	24.8 ... 25.2

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



Published by
OSRAM Opto Semiconductors GmbH
 Leibnizstraße 4, D-93055 Regensburg
www.osram-os.com
 © All Rights Reserved.

EU RoHS and China RoHS compliant product



此产品符合欧盟 RoHS 指令的要求；
 按照中国的相关法规和标准，不含有毒有害物质或元素。

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components ¹, may only be used in life-support devices or systems ² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Phototransistors](#) category:

Click to view products by [OSRAM](#) manufacturer:

Other Similar products are found below :

[QSD123A4R0](#) [ASDL-6620-C22](#) [OED-ST-8LR2](#) [OED-STR44B90-TR](#) [IDCHIP001](#) [PT-A1-AC-3-PE-850](#) [PT-A1-AC-3528-850](#) [PT-A1-AC-5-HE-850](#) [PT-A1-DC-5-BN-940](#) [PT-A1-FC-5-BE-940](#) [PT-A2-AC-3-BE-850](#) [PT-A2-AC-5-BE-850](#) [PT-A2-AC-5-PE-850](#) [PT-A2-AC-5-PN-850](#) [PT-A2-DC-3-BE-940](#) [PT-A4-AC-5-PN-850](#) [PT-A6-AC-5-BN-520](#) [PT-A6-AC-5-PN-520](#) [PT-A8-AC-1206-850](#) [PT-B1-DC-0603-940](#) [PT-IC-AC-3-PE-550](#) [PT-IC-AC-5-BN-520](#) [PT-IC-AC-5-PE-550](#) [PT-IC-AC-5-PN-520](#) [PT-IC-BC-3-PE-550](#) [PT-IC-BC-5-PE-550](#) [140814240010](#) [140814241110](#) [140814240110](#) [140814241010](#) [140817141010](#) [140817140410](#) [140817140010](#) [140817141410](#) [140817140110](#) [140817140210](#) [140817140310](#) [140817141210](#) [140817141110](#) [140817141310](#) [140356145200](#) [140356145300](#) [140814242100](#) [140814242000](#) [140814243000](#) [140354245000](#) [140356145400](#) [140356145000](#) [140814243100](#) [140354245100](#)